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U.S. UTILITY Patent Application

<p>PD</p> <p>SCANNED <u>SAD</u> Q.A. <u>YIT</u></p>	<p>O.I.P.E.</p>	<p>PATENT DATE</p>
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APPLICATION NO. 09/747779	CONT/PRIOR D	CLASS 438	SUBCLASS 257 ⁺	ART UNIT 1765 2811	EXAMINER PIENRO-CRES
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APPLICANTS

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Hong Kim

Fabrication method and structure for ferroelectric nonvolatile memory field effect transistor

PTO-2040
12/89[illegible]

<input type="checkbox"/> TERMINAL DISCLAIMER	DRAWINGS		CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims
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